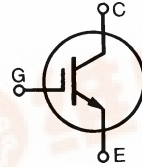




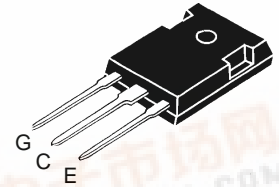
High Voltage, Low $V_{CE(sat)}$ IGBT IXSH 45N120

$V_{CES} = 1200\text{ V}$
 $I_{C25} = 75\text{ A}$
 $V_{CE(sat)} = 3\text{ V}$

Short Circuit SOA Capability



Symbol	Test Conditions	Maximum Ratings	TO-247 AD
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	1200 V	
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 1\text{ M}\Omega$	1200 V	
V_{GES}	Continuous	± 20 V	
V_{GEM}	Transient	± 30 V	
I_{C25}	$T_C = 25^\circ\text{C}$, limited by leads	75 A	
I_{C90}	$T_C = 90^\circ\text{C}$	45 A	
I_{CM}	$T_C = 25^\circ\text{C}$, 1 ms	180 A	
SSOA (RBSOA)	$V_{GE} = 15\text{ V}$, $T_J = 125^\circ\text{C}$, $R_G = 2.7\ \Omega$ Clamped inductive load, $L = 30\ \mu\text{H}$	$I_{CM} = 90$ @ $0.8\ V_{CES}$	A
t_{SC} (SCSOA)	$V_{GE} = 15\text{ V}$, $V_{CE} = 0.6 \cdot V_{CES}$, $T_J = 125^\circ\text{C}$ $R_G = 22\ \Omega$, non repetitive	10	μs
P_C	$T_C = 25^\circ\text{C}$	300	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight		6	g
	Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$



G = Gate, C = Collector, E = Emitter, TAB = Collector

Features

- International standard package JEDEC TO-247
- High frequency IGBT with guaranteed Short Circuit SOA capability
- Fast Fall Time for switching speeds up to 20 kHz
- 2nd generation HDMOS™ process
- Low $V_{CE(sat)}$
 - for minimum on-state conduction losses
- MOS Gate turn-on
 - drive simplicity

Applications

- AC motor speed control
- DC servo and robot drive
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies
- Welding

Advantages

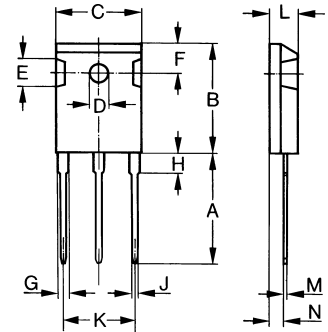
- Easy to mount with 1 screw (isolated mounting screw hole)
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 3\text{ mA}$, $V_{GE} = 0\text{ V}$	1200		V
$V_{GE(th)}$	$I_C = 4\text{ mA}$, $V_{CE} = V_{GE}$	4	6	8 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$, $V_{GE} = 0\text{ V}$			400 μA 1.2 mA
				$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$
I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = \pm 20\text{ V}$			$\pm 100\text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}$, $V_{GE} = 15\text{ V}$			3 V



Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$I_C = I_{C90}$; $V_{CE} = 10\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$		26	S
$I_{C(on)}$	$V_{GE} = 15\text{ V}$, $V_{CE} = 10\text{ V}$		170	A
C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		4150	pF
C_{oes}			285	pF
C_{res}			65	pF
Q_g	$I_C = I_{C90}$, $V_{GE} = 15\text{ V}$, $V_{CE} = 0.5 V_{CES}$		150	200 nC
Q_{ge}			45	60 nC
Q_{gc}			75	100 nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C90}$, $V_{GE} = 15\text{ V}$, $L = 100\ \mu\text{H}$ $V_{CE} = 0.8 V_{CES}$, $R_G = 2.7\ \Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$, higher T_J or increased R_G		80	ns
t_{ri}			250	ns
$t_{d(off)}$			400	ns
t_{fi}			1000	ns
E_{off}			21	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C90}$, $V_{GE} = 15\text{ V}$, $L = 100\ \mu\text{H}$ $V_{CE} = 0.8 V_{CES}$, $R_G = 2.7\ \Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$, higher T_J or increased R_G		80	ns
t_{ri}			250	ns
E_{on}			7.1	mJ
$t_{d(off)}$			450	ns
t_{fi}			1200	ns
E_{off}		27	mJ	
R_{thJC}				0.42 K/W
R_{thCK}			0.25	K/W

TO-247 AD (IXSH) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

Fig.1 Saturation Characteristics

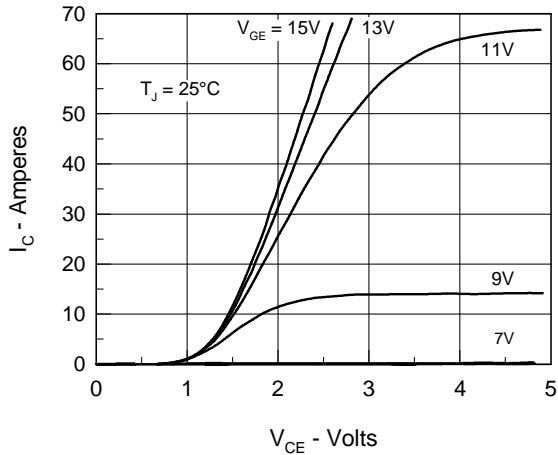


Fig.2 Output Characteristics

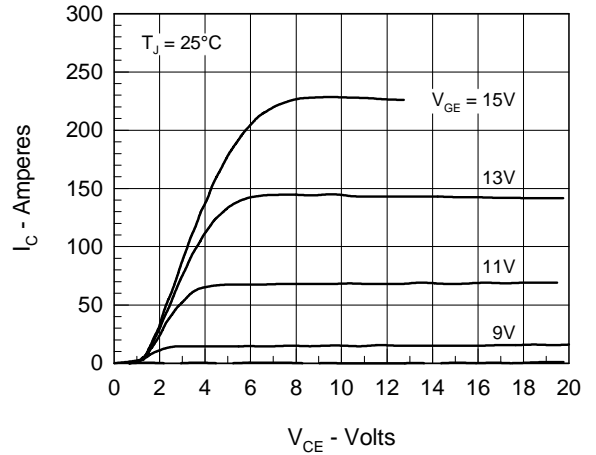


Fig.3 Collector-Emitter Voltage vs. Gate-Emitter Voltage

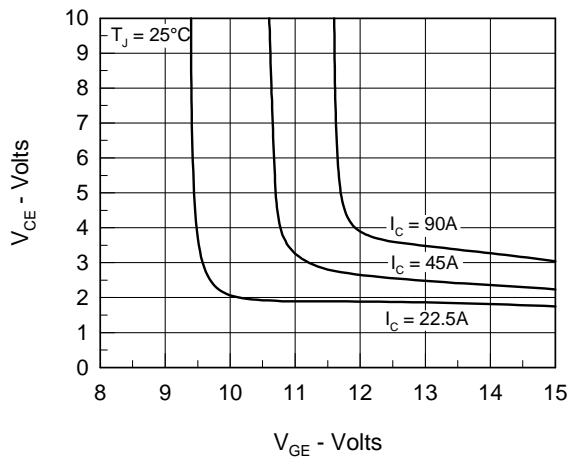


Fig.4 Temperature Dependence of Output Saturation Voltage

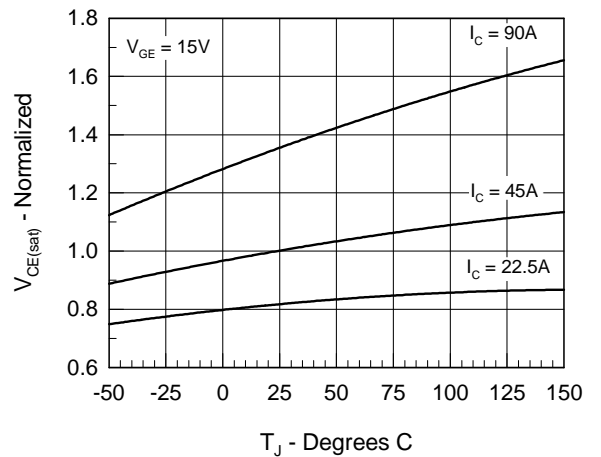


Fig. 5 Input Admittance

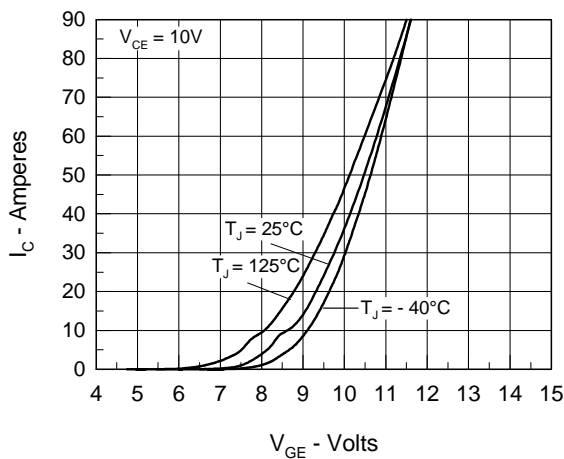


Fig.6 Temperature Dependence of Breakdown and Threshold Voltage

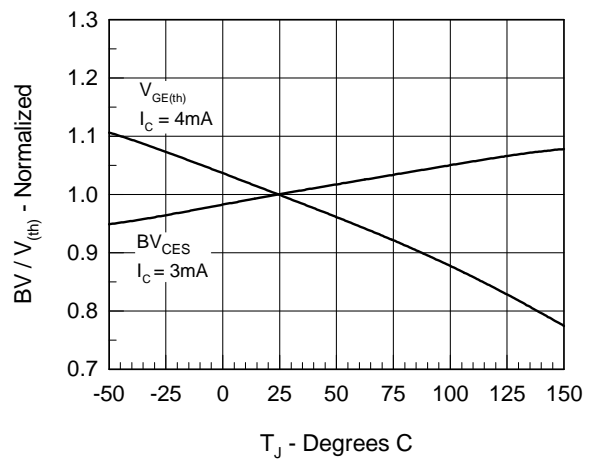


Fig.7 Turn-Off Energy per Pulse and Fall Time on Collector Current

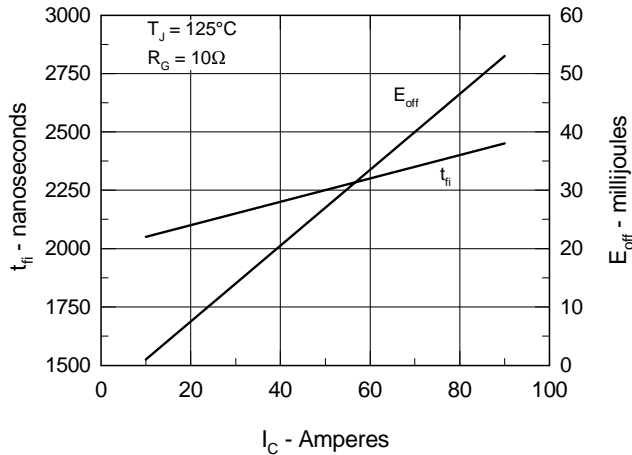


Fig.9 Gate Charge Characteristic Curve

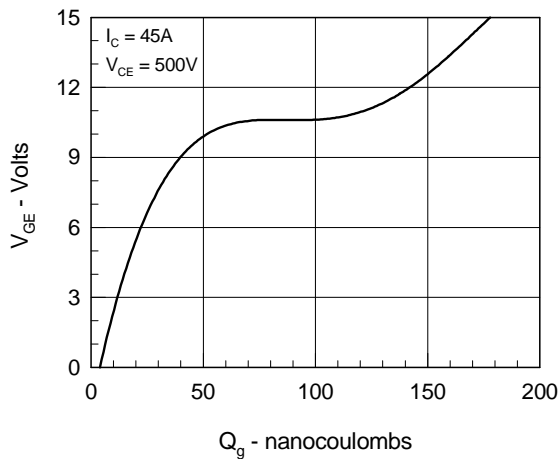


Fig.11 Transient Thermal Impedance

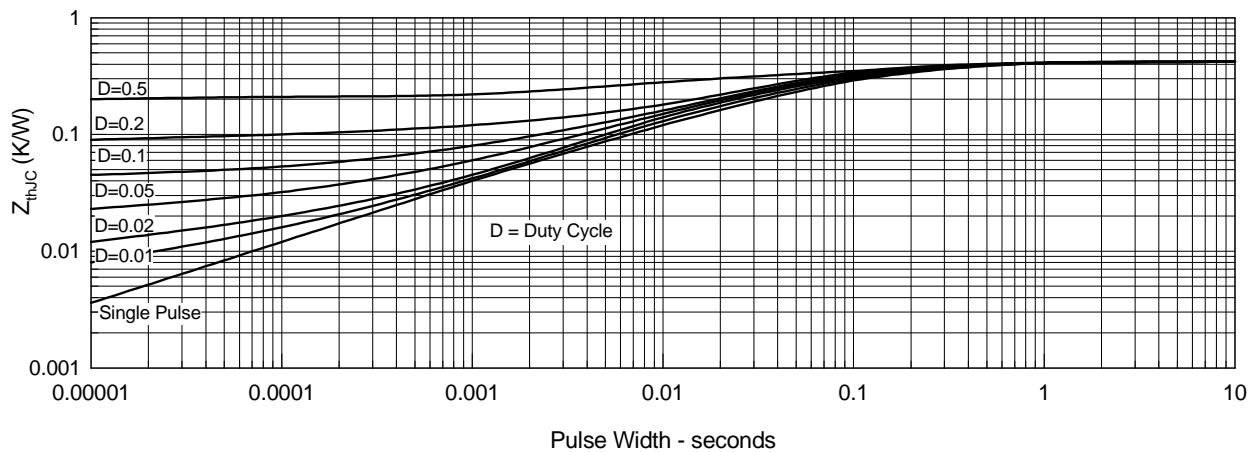


Fig.8 Dependence of Turn-Off Energy Per Pulse and Fall Time on R_G

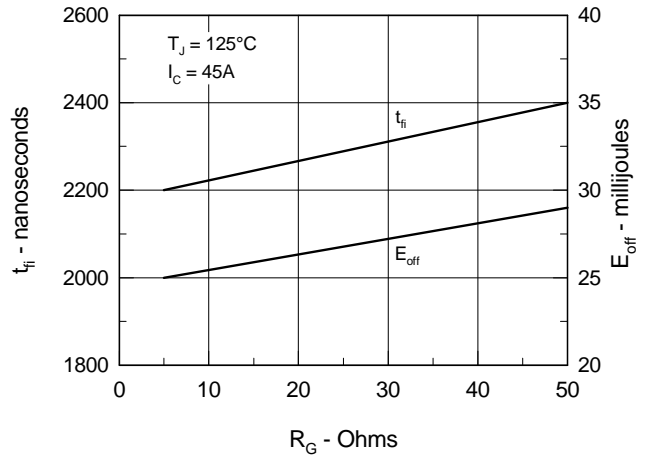


Fig.10 Turn-Off Safe Operating Area

